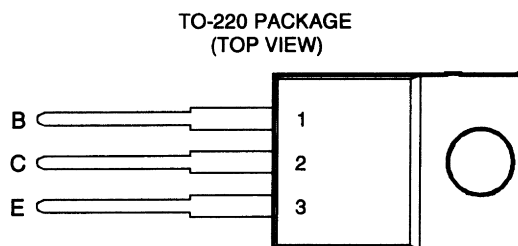


BDT60, BDT60A, BDT60B, BDT60C
PNP SILICON POWER DARLINGTONS

- **Designed for Complementary Use with BDT61, BDT61A, BDT61B and BDT61C**
- **50 W at 25°C Case Temperature**
- **4 A Continuous Collector Current**
- **Minimum h_{FE} of 750 at 1.5 V, 3 A**

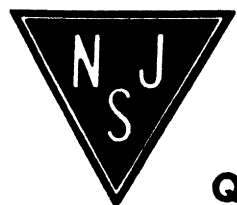


Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	BDT60	V_{CBO}	-60	V
	BDT60A		-80	
	BDT60B		-100	
	BDT60C		-120	
Collector-emitter voltage ($I_B = 0$)	BDT60	V_{CEO}	-60	V
	BDT60A		-80	
	BDT60B		-100	
	BDT60C		-120	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-4	A
Continuous base current		I_B	-0.1	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)		P_{tot}	50	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 2)		P_{tot}	2	W
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Operating free-air temperature range		T_A	-65 to +150	°C

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.
2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.



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electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -30 \text{ mA}$ $I_B = 0$ (see Note 3) BDT60 BDT60A BDT60B BDT60C	-60 -80 -100 -120			V
I_{CEO} Collector-emitter cut-off current	$V_{CE} = -30 \text{ V}$ $I_B = 0$ $V_{CE} = -40 \text{ V}$ $I_B = 0$ $V_{CE} = -50 \text{ V}$ $I_B = 0$ $V_{CE} = -60 \text{ V}$ $I_B = 0$ BDT60 BDT60A BDT60B BDT60C			-0.5 -0.5 -0.5 -0.5	mA
I_{CBO} Collector cut-off current	$V_{CB} = -60 \text{ V}$ $I_E = 0$ $V_{CB} = -80 \text{ V}$ $I_E = 0$ $V_{CB} = -100 \text{ V}$ $I_E = 0$ $V_{CB} = -120 \text{ V}$ $I_E = 0$ $V_{CB} = -30 \text{ V}$ $I_E = 0$ $T_C = 150^\circ\text{C}$ $V_{CB} = -40 \text{ V}$ $I_E = 0$ $T_C = 150^\circ\text{C}$ $V_{CB} = -50 \text{ V}$ $I_E = 0$ $T_C = 150^\circ\text{C}$ $V_{CB} = -60 \text{ V}$ $I_E = 0$ $T_C = 150^\circ\text{C}$ BDT60 BDT60A BDT60B BDT60C BDT60 BDT60A BDT60B BDT60C			-0.2 -0.2 -0.2 -0.2 -2.0 -2.0 -2.0 -2.0	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5 \text{ V}$ $I_C = 0$			-5	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -3 \text{ V}$ $I_C = -1.5 \text{ A}$ (see Notes 3 and 4)	750			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -6 \text{ mA}$ $I_C = -1.5 \text{ A}$ (see Notes 3 and 4)			-2.5	V
$V_{BE(on)}$ Base-emitter voltage	$V_{CE} = -3 \text{ V}$ $I_C = -1.5 \text{ A}$ (see Notes 3 and 4)			-2.5	V
V_{EC} Parallel diode forward voltage	$I_E = -1.5 \text{ A}$ $I_B = 0$			-2.0	V

NOTES: 3. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			2.5	$^\circ\text{C/W}$
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	$^\circ\text{C/W}$

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS [†]	MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = -2 \text{ A}$ $I_{B(on)} = -8 \text{ mA}$ $I_{B(off)} = 8 \text{ mA}$		1		μs
t_{off} Turn-off time	$V_{BE(off)} = 5 \text{ V}$ $R_L = 20 \Omega$ $t_p = 20 \mu\text{s}$, dc $\leq 2\%$		4.5		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



Quality Semi-Conductors